

TO-92 Plastic-Encapsulate Transistors

2SA1515 TRANSISTOR (PNP)

FEATURES

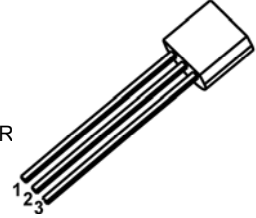
- Low Collector-Emitter Saturation Voltage
- Low Transition Frequency

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-32	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-1	A
P _C	Collector Power Dissipation	500	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	250	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

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1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.05mA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-32			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.05mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V, I _E =0			-0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.5	μA
DC current gain	h _{FE}	V _{CE} =-3V, I _C =-0.1A	82		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-0.5A, I _B =-0.05A			-0.5	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			30	pF
Transition frequency	f _T	V _{CE} =-5V, I _C =-50mA	50			MHz

CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82-180	120-270	180-390